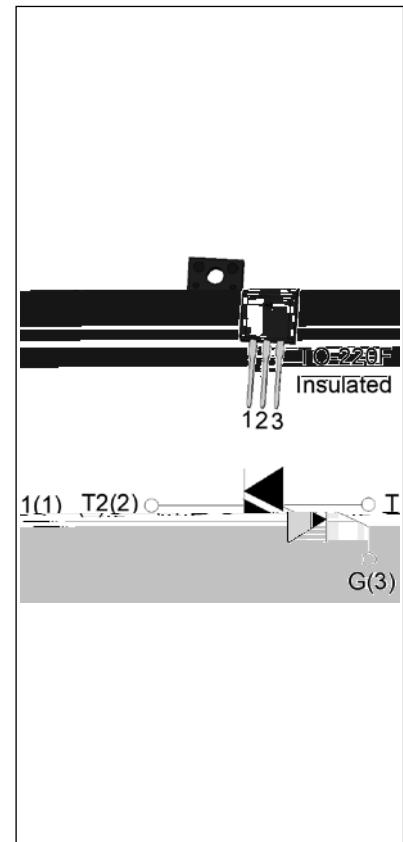


T835H-10F 8A TRIAC

Rev.A.1.0

DESCRIPTION:

The T835H-10F triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T835H-10F provides a very high switching capability up to junction temperatures of 150°C. By using an external plastic package, T835H-10F provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.


MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	8	A
V_{DRM}/V_{RRM}	1000	V
$I_{GT\ I/II/III}$	35/35/35	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	°C
Operating junction temperature range	T_j	-40-150	°C
Repetitive peak off-state voltage ($T_j=25^\circ\text{C}$)	V_{DRM}	1000	V
Repetitive peak reverse voltage ($T_j=25^\circ\text{C}$)	V_{RRM}	1000	V
RMS on-state current ($T_c \leq 113^\circ\text{C}$)	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle , $t_p=20\text{ms}$, $T_j=25^\circ\text{C}$)	I_{TSM}	80	A
Non repetitive surge peak on-state current (full cycle , $t_p=16.6\text{ms}$, $T_j=25^\circ\text{C}$)		88	
I^2t value for fusing ($t_p=10\text{ms}$, $T_j=25^\circ\text{C}$)	I^2t	32	A^2s
Critical rate of rise of on-state current ($I_G=2\ I_{GT}$, $f=100\text{Hz}$, $T_j=150^\circ\text{C}$)	di/dt	100	A s
Peak gate current ($t_p=20\ \text{s}$, $T_j=150^\circ\text{C}$)	I_{GM}	4	A

Average gate power dissipation ($T_j=150^\circ\text{C}$)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	10	W
Peak pulse voltage ($T_j=25^\circ\text{C}$; non-repetitive, off-state; FIG.7)	V_{pp}	4	kV

ELECTRICAL CHARACTERISTICS ($T_j=25^\circ\text{C}$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12\text{V } R_L=33$	I - II - III	MAX.	35	mA
V_{GT}		I - II - III	MAX.	1	V
V_{GD}	$V_D=V_{DRM} T_j=150^\circ\text{C}$ $R_L=3.3\text{K}$	I - II - III	MIN.	0.2	V
I_L	$I_G=1.2I_{GT}$	I - III	MAX.	50	mA
		II		70	
I_H	$I_T=100\text{mA}$		MAX.	45	mA
dV/dt	$V_D=670\text{V}$ Gate Open $T_j=150^\circ\text{C}$		MIN.	800	V s
$(dI/dt)_c$	$j=150^\circ\text{C}$		MIN.	5	A/ms
t_{on}	$I_G=40\text{mA } I_A=200\text{mA } I_R=20\text{mA}$ $T_j=25^\circ\text{C}$		TYP.	3	s
t_{off}				30	

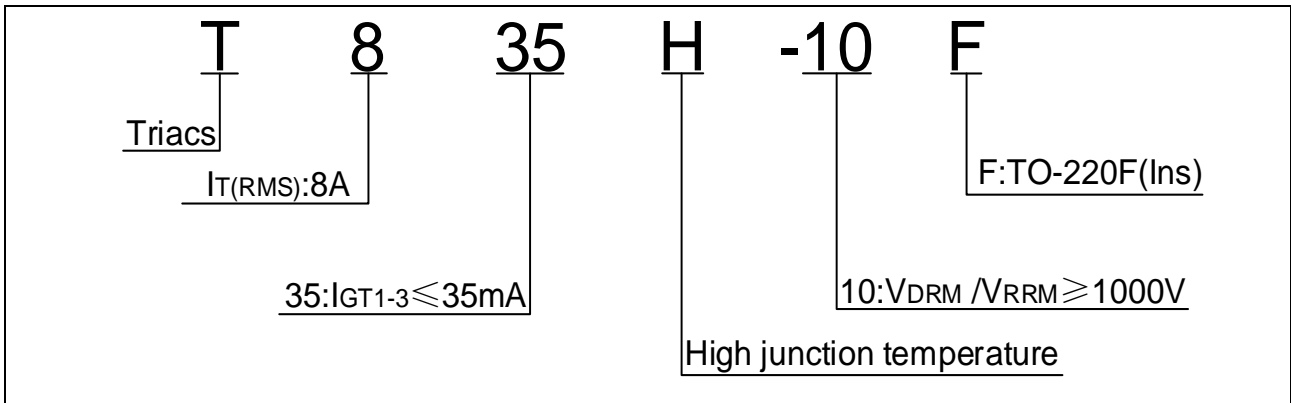
STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=11\text{A } t_p=380 \text{ s}$	$T_j=25^\circ\text{C}$	1.4	V
V_{TO}	Threshold voltage	$T_j=150^\circ\text{C}$	0.77	V
R_D	Dynamic resistance	$T_j=150^\circ\text{C}$	52.6	
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^\circ\text{C}$	5	A
I_{RRM}		$T_j=150^\circ\text{C}$	2	mA

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	3.5	$^\circ\text{C/W}$
$R_{th(j-a)}$	junction to ambient (AC)	60	$^\circ\text{C/W}$

ORDERING INFORMATION



MARKING

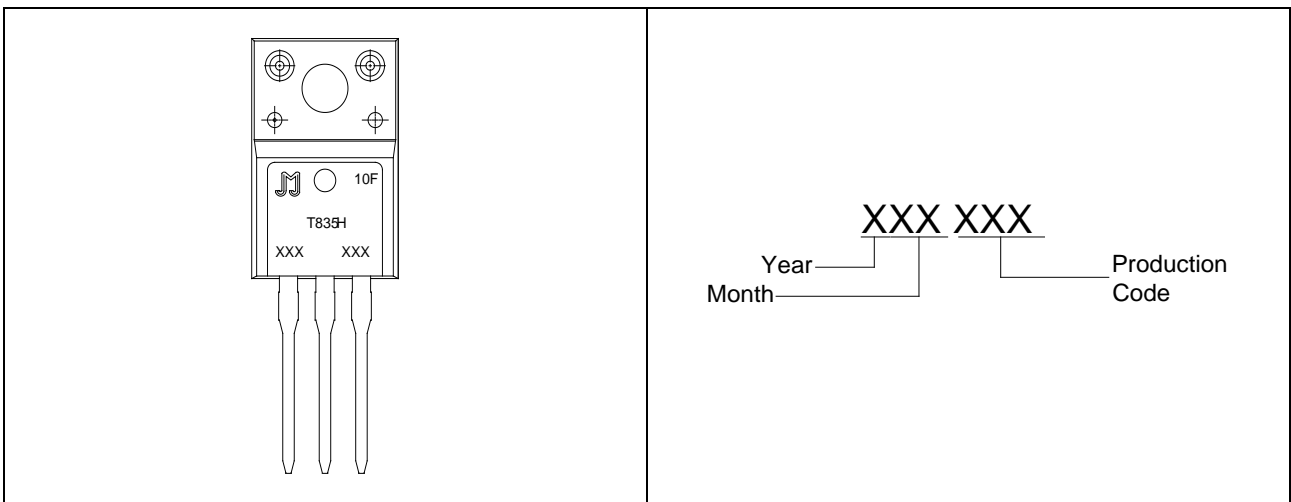


FIG.1 Maximum power dissipation versus RMS on-state current

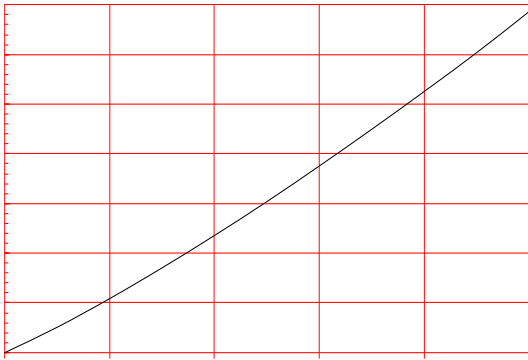


FIG.2: RMS on-state current versus case temperature

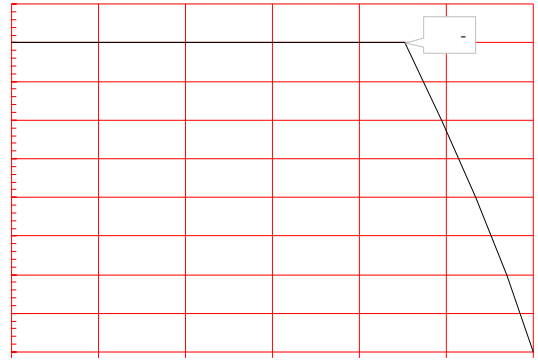


FIG.3: Surge peak on-state current versus number of cycles

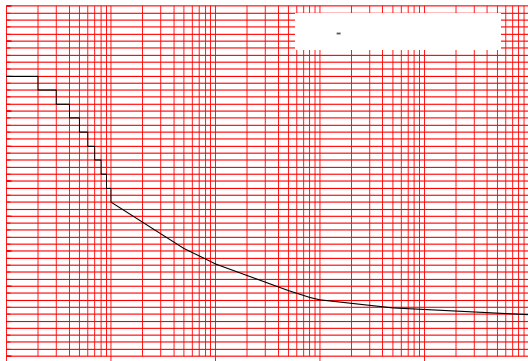
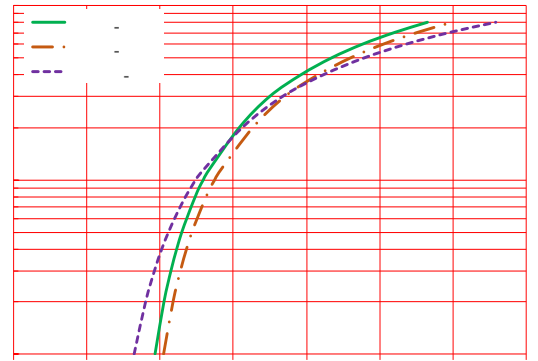


FIG.4: On-state characteristics



pd“ ÖI f

ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		H- I- J			
T835H-10F	1000	35	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.10, 2023	A.1.0	Last updated

Information furnished in this document is believed to be accurate and reliable. However, Jiangsu JieJie Microelectronics Co., Ltd. assumes no responsibility for the consequences of use without consideration for such information nor use beyond it. Information mentioned in this document is subject to change without notice, apart from that when an agreement is signed, Jiangsu JieJie complies with the agreement.

Products and information provided in this document have no infringement of patents. Jiangsu JieJie assumes no responsibility for any infringement of other rights of third parties which may result from the use of such products and information. This document supersedes and replaces all information previously supplied.

 is a registered trademark of Jiangsu JieJie Microelectronics Co., Ltd.

Copyright ©2023 Jiangsu JieJie Microelectronics Co., Ltd. Printed All rights reserved.